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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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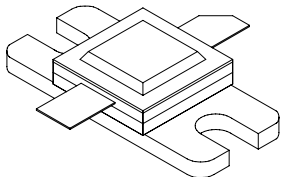
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JTDB75

75 Watts, 36 Volts, Pulsed
Avionics 960 - 1215 MHz

<p>GENERAL DESCRIPTION</p> <p>The JTDB75 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.</p>	<p>CASE OUTLINE 55AW, Style 1</p> 
<p>ABSOLUTE MAXIMUM RATINGS</p> <p>Maximum Power Dissipation Device Dissipation @25°C² 220 W</p> <p>Maximum Voltage and Current Collector to Base Voltage (BV_{ces}) 55 V Emitter to Base Voltage (BV_{ebo}) 3.5 V Collector Current (I_c) 8.0 A</p> <p>Maximum Temperatures Storage Temperature -65 to +200 °C Operating Junction Temperature +200 °C</p>	

ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Out	F = 960-1215 MHz	75			W
P _{in}	Power Input	V _{cc} = 36 Volts			15	W
P _g	Power Gain	PW = 10 μsec, Note 1	7.0	8.2		dB
η _c	Collector Efficiency	DF = 40%, Note 1		40		%
VSWR ¹	Load Mismatch Tolerance	F = 1090 MHz			3:1	

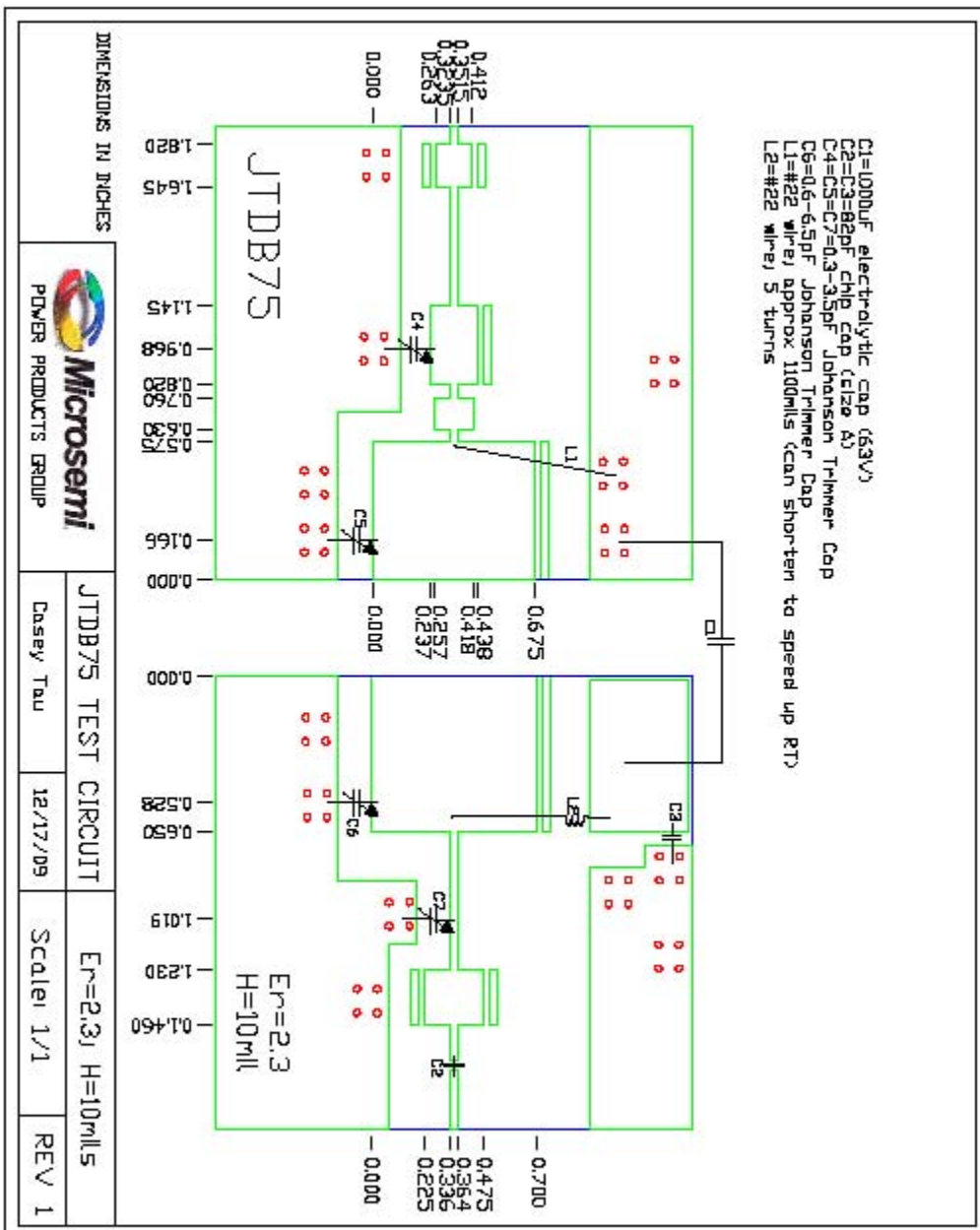
FUNCTIONAL CHARACTERISTICS @ 25°C

BV _{ebo}	Emitter to Base Breakdown	I _e = 30 mA	3.5			V
BV _{ces}	Collector to Emitter Breakdown	I _c = 30 mA	55			V
h _{FE}	DC – Current Gain	V _{ce} = 5V, I _c = 1A	20		100	
θ _{jc} ²	Thermal Resistance				0.8	°C/W

NOTE 1: At rated output power and pulse conditions

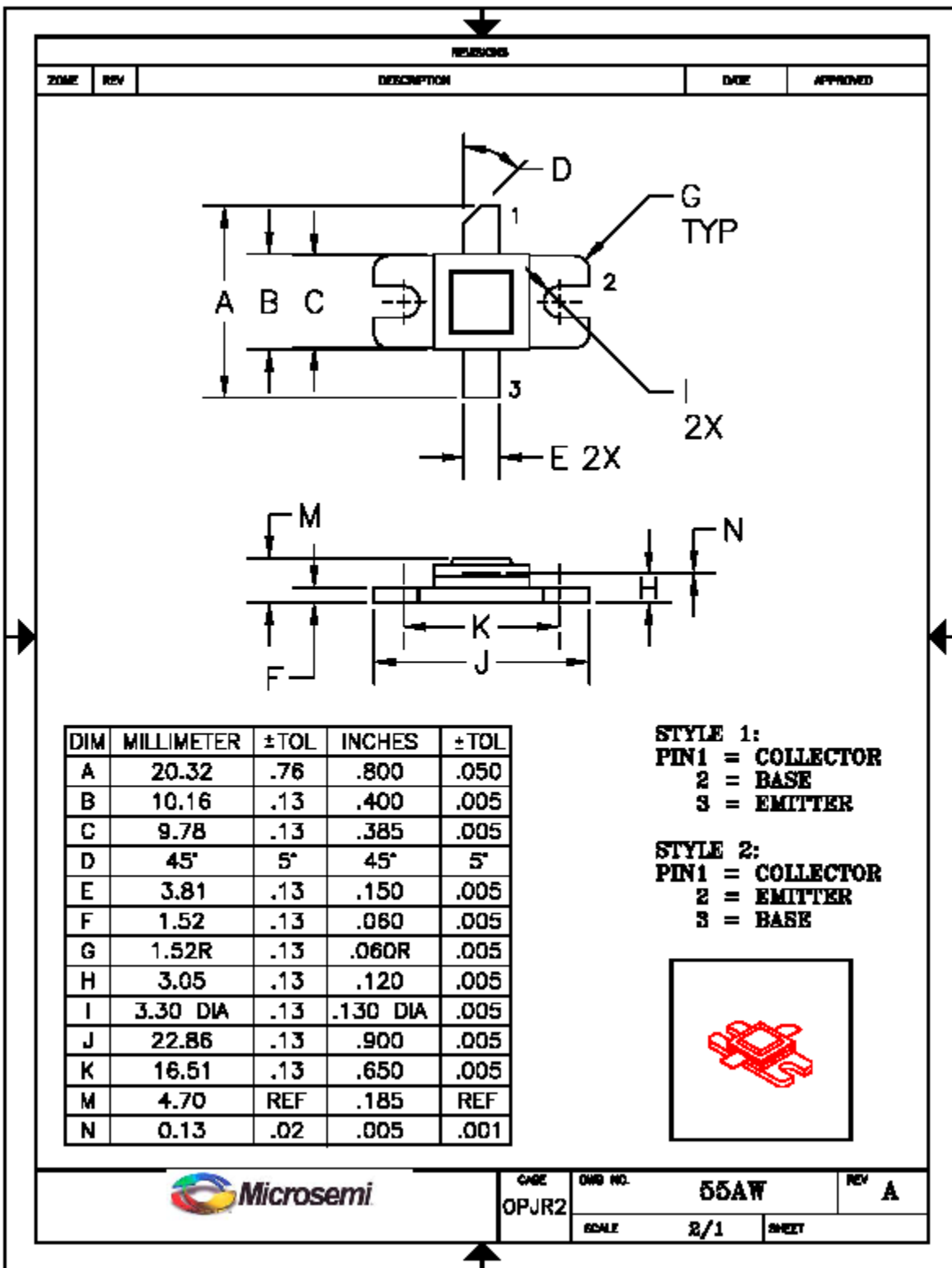
2. At rated pulse conditions

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